Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1039	257/355,356,360,361,362.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 09:46
L3	734	L2 and @ad<"20020712"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 09:54
L4	1413	438/289,301,514,200.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 09:54
L5	827	L4 and @ad<"20020712"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 09:54
S1	0	electrostatic adj discharge adj protect$3 and offset adj transistor and increase near5 acceptor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:27
S2	7	electrostatic adj discharge adj protect$3 and increase near5 acceptor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:38
S3	59	electrostatic adj discharge adj protect$3 and reduce near3 breakdown adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:38
S4	41	S3 and @ad<"20020712"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 09:46

S5	1	@pn="5897348"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 09:46
S6	1	@pn="6040222"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 14:47
S7	1	@pn="5744841"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 15:33
S8	240	(ESD (electrostatic adj discharge adj protect$3)) and (LDD (lightly adj doped adj drain)) same (NMOS NMOST NMOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 15:13
S9	201	S8 and @ad<"20020712"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 15:13
S10	1	@pn="6218226"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 15:33